Correlated vortex pinning in Si-nanoparticle doped M gB₂

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The magnetoresistivity and critical current density of well characterized Sinanoparticle doped and undoped Cu-sheathed M gB₂ tapes have been measured at temperatures T 28 K in magnetic elds B 0:9 T. The inneversibility line B_{irr}(T) for doped tape shows a stepw ise variation with a kink around 0.3 T. Such B_{irr}(T) variation is typical for high-temperature superconductors with columnar defects (a kink occurs near the matching eld B) and is very dierent from a smooth B_{irr}(T) variation in undoped M gB₂ sam ples. The microstructure studies of nanoparticle doped M gB₂ sam ples show uniform ly dispersed nanoprecipitates, which probably act as a correlated disorder. The observed dierence between the eld variations of the critical current density and pinning force density of the doped and undoped tape supports the above ndings.

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IN T R O D U C T IO N

The discovery of superconductivity in M gB₂ com pound [1] has aroused a great deal of interest in the scientic community [2]. Compared to high-temperature superconductors (HTS), MgB2 has a lower transition tem perature T_c ' 39 K, but its sim ple com position, abundance of constituents and the absence of weak intergranular links [3, 4, 5] m ake the M gB₂ a prom ising m aterial for appli-20 K, which is above $T_c s$ of conventional cations at T superconductors (LTS). Indeed, the simple preparation and rather high critical currents J_c of composite M gB₂ tapes and wires [4, 6, 7, 8, 9] lend strong support to these expectations. Unfortunately, com pared to practical LT S (NbTi, Nb₃Sn), MgB₂ exhibits weak ux-pinning [2, 10], which results in strong eld dependence of J_c and a low irreversibility eld B_{irr} (4:2 K) 8T [2].

Several techniques, such as alloying [11, 12, 13], particle irradiation [14, 15, 16, 17] and mechanical processing [9, 18] have been employed in order to improve the ux-pinning in M gB₂, but with limited success. In particular, proton irradiation [14] increased B irr at 20 K, but also suppressed low - eld J_c, whereas alloying seem s to enhance J_c , but has little e ect on B _{irr} [12, 13]. Better results were recently obtained by adding nanoparticles to $M gB_2$ [19, 20, 21]. It appears that a variety of nanoparticles considerably enhance the ux-pinning in M gB₂ over a wide tem perature range T 30 K . In particular, the addition of 10 wt% of SiC nanoparticles [20] yielded B_{irr} (42K) & 12T, which is higher than that of optimized NbTi [22]. The actual mechanism of the uxpinning enhancem ent upon nanoparticle doping of MgB₂ is not well understood at present.

Here we present the results for magnetoresistance R (T;B) and critical current I_c (T;B) of MgB₂ tape doped with Sinanoparticles, which reveal the uxpinning mechanism associated with nanoparticle doping.

In particular, B_{irr} (T) of doped sample shows a kink at B_{irr} 0:3 T, which is the signature of vortex pinning at correlated defects [23], whereas no kink is observed in undoped sample. The variation of critical current and pinning force density $F_p = J_c B$ with the eld and temperature also show di erent pinning mechanisms in doped and undoped M gB₂, respectively.

EXPERIM ENTAL PROCEDURES

Cu-sheathed MgB2 tapes were prepared by in-situ powder-in-tube method [8]. In the doped tape, in addition to M g and B, 5 wt% of Sinanoparticles with an average size 50 nm was added. A low sintering tem perature (670 { 690 C) and a short sintering time (severalm inutes) were em ployed [21] in order to avoid di usion of Cu into the M gB_2 core [24]. This resulted in rather porous, low density (50%) cores. The core cross-sections were elipticalwith areas 4:95 10³ and 4:8 10³ cm² for the doped and undoped tape, respectively. The sam ple lengths were approximately 1.5 cm and the voltage and current leads were soldered on Cu-sheathing. The magnetoresistance was measured with low-frequency ac method [5, 15] for 0:9 T perpendicular Τ 28 K in magnetic eld B to a broad face of the tape and the current direction. $I_{RM S} = 1 \text{ mA}$ was used and the voltage resolution was 0.3 nV.C ritical currents were measured on samples used in R (T; B) measurements with the pulse method (sawtooth pulse with duration less than 10 m s and peak current of 200 A [8]).

RESULTS AND DISCUSSION

T he variation of the resistance with tem perature (28 T 300 K) for our undoped and Sidoped tape (Fig. 1)



FIG.1: Tem perature variation of the electrical resistance for the undoped (lower) and doped (upper curve) sample.

are typical for Cu-clad M gB₂ w ires [24], with a larger resistance of the doped sample due to a larger distance between its voltage contacts.

Fig. 2 compares the superconducting transitions in elds B 0:9 T for undoped and doped sample. As in other com posite superconductors [25], the shape of these transitions is a ected by Cu-sheathing. How ever, the onset of resistance (hence $T_c (R ! 0) = T_{c0}$) is not a ected by sheathing [25], and the zero-eld $T_{c0} = 382$ K for the undoped tape (Fig. 2a) is typical for bulk $M gB_2$ samples [2, 5, 24]. A strong shift of its T_{c0} with magnetic eld (i.e. $T_{irr}(B)$) re ects a weak ux-pinning in the undoped MgB2. For the doped sample (Fig. 2b), zero-eld $T_{c0} = 36:4$ K is lower than that of the undoped one, but the shift of its T_{c0} with eld is considerably smaller, which indicates an enhancement of ux-pinning (the expansion of the vortex-solid regim e). Furtherm ore, values of T_{c0} for the doped sample in B . 0:3 T are compressed within a rather narrow temperature interval, whereas those for the undoped one are more evenly spread throughout the explored eld range.

Fig. 3 com pares the irreversibility elds B_{irr} (T) (dened by using the low-resistivity criterion $_{\rm c} = 5$ n cm) for our samples. For the undoped tape, both the magnitude and temperature variation of B_{irr} are the same as the literature data for M gB₂ samples [2, 5, 16, 24, 26]. In particular, our values of B_{irr} (T) are equal to those obtained from the onset of the third harmonic in the low-frequency ac susceptibility of a dense M gB₂ sample [26]. Approximately linear, B_{irr} (T) variation for T 36 K extrapolates to B_{irr} (4.2 K) 8.4 T, which is a typical value for bulk M gB₂ [2].

The B $_{\rm irr}$ (T) variation for the doped tape is very different from that of the undoped one (Fig. 3). Here, B $_{\rm irr}$ increases rapidly with decreasing temperature down to 35.5 K, and shows slower, linear variation for T 35



FIG.2: Temperature variation of the electrical resistance in magnetic elds B = 0, 0.01, 0.02, 0.04, 0.07, 0.1, 0.14, 0.2, 0.3, 0.4, 0.5, 0.6, 0.7, 0.8 and 0.9 T for the a) undoped and b) doped sample.



FIG. 3: Temperature dependence of the irreversibility eld $B_{\rm irr}$ for the undoped (empty) and doped (full squares) sam – ple. Inset: the same dependence, but vs. the reduced tem – perature $t_{\rm irr} = T_{\rm irr}$ (B)= $T_{\rm irr}$ (O).

K. Such a stepw ise $B_{irr}(T)$ variation is speci c for HTS containing columnar defects [23, 27, 28, 29], where the crossover in $B_{irr}(T)$ occurs around the matching eld B, which is the eld at which the vortex and columnar defect density n are equal (B = n _0, _0 being the ux quantum [28, 29]). This crossover occurs because the pinning of interstitial vortices for $B_{irr} > B$ is less weaker than for vortices residing onto the columns for $B_{irr} < B$.

From our crossover eld B_c B_{irr} (35.5 K) ' 0.3 T we estimate n 1:4 10^4 m ², and the average distance between defects 80 nm. The m icrostructural studies of the nanoparticle doped M gB₂ [19, 20, 21] show nely dispersed precipitates within the M gB₂ m atrix with sizes

10 nm. For Si and SiC doped M gB₂ [20, 21] these precipitates are mainly M g₂Si phase, and their average spacing is comparable to that estimated above. Therefore in our tape M g₂Si nanoprecipitates, resulting from the reaction of Si-nanoparticles and M g during the sintering, act analogously to colum nar defects in HTS. This outcom e appears rather surprising considering di erent nature and geometries of precipitates and colum ns, as well as the di erent nature of vortices [23, 30] in these materials. However, the matching e ects are common in type-II superconductors [31] and are not specific only to HTS.

A linear variation of B_{irr} (T) for T 35 K in the doped sam ple extrapolates to B_{irr} (42 K) ' 11:5 T, which is consistent with the other results for nanoparticle-doped M gB₂ [19, 20, 21], and is higher than B_{irr} (42 K) for NbT i. However, for T > 33 K, B_{irr} of the doped sam – ple is lower than that for the undoped sam ple, which is entirely due to its lower zero- eld T_{c0}. Indeed, a plot of B_{irr} vs. reduced tem perature t_{irr} = T_{irr} (B)=T_{irr} (0) for both sam ples (inset to Fig. 3) show s that for all values of t_{irr}, B_{irr} of the doped sam ple is higher than that of the undoped one. Therefore, vortex pinning in nanoparticle doped M gB₂ is enhanced with respect to that in undoped M gB₂ at all reduced tem peratures.

D i erent vortex pinning m echanism s in our tapes im ply also dierent eld variations of their J_c and F_p = $J_{c}B$. Fig. 4 compares the $J_{c}(B)$ variations of our sam – 33 K. The undoped tape (Fig. 4a) shows ples for T approximately exponential J_c (B) variation, which is typical for M gB₂ sam ples [2, 10, 14, 20]. At low tem peratures (high I_c), large self-eld $_0H_s$ (H $_s$ ' $I_c=c$, where c is the circum ference of the core) m akes $J_c (B < _0H_s)$ nearly constant, whereas at elevated elds (B ! B irr) J_c rapidly decreases to zero. From the experimental J_{c} (B;T) curves (Fig. 4a) we obtained F_{p} (B;T) ones, from which we determ ined the elds $B_{max}(T)$ at which the volum e pinning force density reaches its maximum value $F_{pmax} = J_c B_{max}$. The eld B_{max} is an important parameter of the vortex pinning within the vortexsolid phase. In particular, in the case of dom inant vortex pinning mechanism, the ratio $B_{max}=B_{irr}$ may re-



FIG.4: Dependence of the critical current density J_c on m agnetic eld B at denoted tem peratures for the a) undoped and b) doped sam ple.

veal this mechanism. For the undoped tape we found $B_{m ax}=B_{irr}$ 0.21, which is similar to that observed in Nb₃Sn [32] and is consistent with a commonly accepted grain boundary pinning mechanism for a bulk M gB₂ [3]. In spite of a probably common vortex pinning mechanism in both bulk M gB₂ and Nb₃Sn, vortex pinning in M gB₂ is apparently weaker (lower $B_{m ax}$ and B_{irr}) than that in Nb₃Sn. The probable reason for that are larger grains, clean and narrow grain boundaries, and quite a large coherence length [30] in M gB₂.

The J_c (B) variation of nanoparticle doped M gB₂ sam – ple (Fig. 4b) is very di erent from that for the undoped tape (Fig. 4a). The S-shaped J_c (B) curves of the doped tape are reminiscent of those observed in HTS lms, tapes and crystals containing columnar defects [23]. Further, for the same reduced temperature $t = T = T_c$, the decrease of J_c with B in the doped tape is considerably smaller than that for the undoped one. A ccordingly, the elds B_{max} (t) are enhanced with respect to those of the undoped tape, which shows that nanoparticle doping enhances vortex pinning throughout the vortex-solid regime [23]. Furtherm ore, the enhancem ent of B_{max} (t) in the doped tape is larger than that of B_{irr} (t), which results in B_{max} (t)=B_{irr} (t) 0.29 for the doped tape. Such B_{max}=B_{irr} ratio is unlikely to arise only from the grain boundary pinning [32] and was earlier observed for HTS tapes [33] with a modest density of colum nar defects (B . 0.2 T). Therefore, we propose that B_{max}=B_{irr} 0.29 arises from the competition of two pinning mechanisms (for example, a grain boundary pinning and a core pinning at nanoprecipitates) as was the case in HTS tapes. A detailed investigation of J_c (B) curves for a number of tem peratures extending over a broad tem perature range (which requires I > 200 A) is necessary in order to solve this problem.

In spite of 50% porosity, our tapes have large self-eld J_cs (Fig. 4), which increase rapidly with decreasing tem – perature (J_c (t) ' J_c (0) (1 t)ⁿ, with n 1:5). In particular, the observed J_c (0:9 T_c) 40 kA/cm² for both tapes extrapolate to J_c (20 K) 350 kA/cm², the value which was con rm ed by the magnetic measurements of J_c (20 K) [21]. Therefore, fully dense M gB₂ tapes are expected [5, 19] to reach J_c (20 K) 10⁶ A/cm², which is above J_c (4.2 K) for the best B i2223/A g tapes.

In summary, we have shown that a uniform dispersion of Mg2Sinanoprecipitates (resulting from the addition of Sinanoparticles to Mg and B powders [20, 21]) not only enhances the ux-pinning in MgB₂ samples, but also introduces an additional pinning mechanism. In particular, we observed a step-wise variation of B_{irr} (T) in nano-Si doped M gB₂ tape with a kink around B ' 0:3 T, which is rem iniscent of the vortex pinning at correlated disorder in HTS [23, 27, 28, 29]. We also observed a corresponding di erence in the shapes of J_c (B) and F_p (B) curves for the doped and undoped tape respectively. A 1though our results were obtained for $M gB_2$ tape doped with Sinanoparticles only, we believe that the above conclusions hold also for other MgB2 samples doped with di erent types of nanoparticles [19, 20, 21], providing that these nanoparticles form uniform ly dispersed nonsuperconducting nanoprecipitates.

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